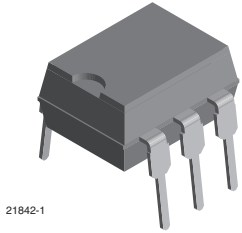
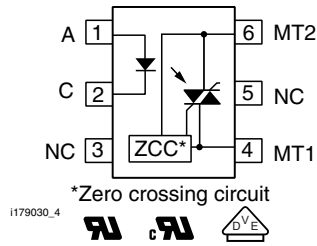


## Optocoupler, Phototriac Output, Zero Crossing, High dV/dt, Low Input Current



21842-1



I179030\_4


**FEATURES**

- High static dV/dt 5 kV/μs
- High input sensitivity  $I_{FT} = 1.6 \text{ mA}, 2 \text{ mA}, \text{ and } 3 \text{ mA}$
- 300 mA on-state current
- Zero voltage crossing detector
- 400 V, and 600 V blocking voltage
- Isolation test voltage 5300  $V_{RMS}$
- Compliant to RoHS Directive 2002/95/EC


**RoHS  
COMPLIANT**
**DESCRIPTION**

The VO4154 and VO4156 consists of a GaAs IRLED optically coupled to a photosensitive zero crossing TRIAC packaged in a DIP-6 package.

High input sensitivity is achieved by using an emitter follower phototransistor and a cascaded SCR predriver resulting in an LED trigger current of 1.6 mA for bin D, 2 mA for bin H, and 3 mA for bin M.

The new phototriac zero crossing family uses a proprietary dV/dt clamp resulting in a static dV/dt of greater than 5 kV/μs.

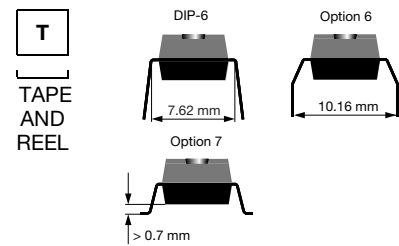
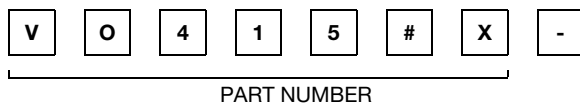
The VO4154 and VO4156 isolates low-voltage logic from 120  $V_{AC}$ , 240  $V_{AC}$ , and 380  $V_{AC}$  lines to control resistive, inductive, or capacitive loads including motors, solenoids, high current thyristors or TRIAC and relays.

**APPLICATIONS**

- Solid-state relays
- Industrial controls
- Office equipment
- Consumer appliances

**AGENCY APPROVALS**

- UL1577, file no. E52744 system code H or J, double protection
- cUL - file no. E52744, equivalent to CSA bulletin 5A
- DIN EN 60747-5-5 (VDE 0884) available with option 1

**ORDERING INFORMATION**


AGENCY CERTIFIED/ PACKAGE	$V_{DRM} 400$			$V_{DRM} 600$		
	TRIGGER CURRENT, $I_{FT}$ (mA)					
UL, cUL	1.6	2	3	1.6	2	3
DIP-6	VO4154D	VO4154H	VO4154M	VO4156D	VO4156H	VO4156M
DIP-6, 400 mil, option 6	VO4154D-X006	VO4154H-X006	VO4154M-X006	VO4156D-X006	VO4156H-X006	VO4156M-X006
SMD-6	VO4154D-X007T	VO4154H-X007T	VO4154M-X007T	VO4156D-X007T	VO4156H-X007T	VO4156M-X007T

ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup> (T <sub>amb</sub> = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	PART	SYMBOL	VALUE	UNIT
<b>INPUT</b>					
Reverse voltage			V <sub>R</sub>	6	V
Forward current			I <sub>F</sub>	60	mA
Surge current			I <sub>FSM</sub>	2.5	A
Power dissipation			P <sub>diss</sub>	100	mW
Derate from 25 °C				1.33	mW/°C
<b>OUTPUT</b>					
Peak off-state voltage		VO4154D/H/M	V <sub>DRM</sub>	400	V
		VO4156D/H/M	V <sub>DRM</sub>	600	V
RMS on-state current			I <sub>TM</sub>	300	mA
Total power dissipation			P <sub>diss</sub>	500	mW
Derate from 25 °C				6.6	mW/°C
<b>COUPLER</b>					
Isolation test voltage (between emitter and detector, climate per DIN 500414, part 2, Nov. 74)	t = 1 min		V <sub>ISO</sub>	5300	V <sub>RMS</sub>
Storage temperature range			T <sub>stg</sub>	- 55 to + 150	°C
Ambient temperature range			T <sub>amb</sub>	- 55 to + 100	°C
Soldering temperature	max. ≤ 10 s dip soldering ≥ 0.5 mm from case bottom		T <sub>sld</sub>	260	°C

**Note**

<sup>(1)</sup> Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

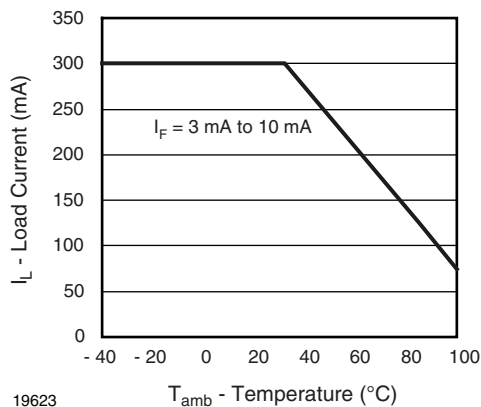


Fig. 1 - Recommended Operating Condition

THERMAL CHARACTERISTICS			
PARAMETER	SYMBOL	VALUE	UNIT
LED power dissipation	$P_{diss}$	100	mW
Output power dissipation	$P_{diss}$	500	mW
Maximum LED junction temperature	$T_{jmax.}$	125	°C
Maximum output die junction temperature	$T_{jmax.}$	125	°C
Thermal resistance, junction emitter to board	$\theta_{JEB}$	150	°C/W
Thermal resistance, junction emitter to case	$\theta_{JEC}$	139	°C/W
Thermal resistance, junction detector to board	$\theta_{JDB}$	78	°C/W
Thermal resistance, junction detector to case	$\theta_{JDC}$	103	°C/W
Thermal resistance, junction emitter to junction detector	$\theta_{JED}$	496	°C/W
Thermal resistance, case to ambient	$\theta_{CA}$	3563	°C/W

**Note**

- The thermal characteristics table above were measured at 25 °C and the thermal model is represented in the thermal network below. Each resistance value given in this model can be used to calculate the temperatures at each node for a given operating condition. The thermal resistance from board to ambient will be dependent on the type of PCB, layout and thickness of copper traces. For a detailed explanation of the thermal model, please reference Vishay's Thermal Characteristics of Optocouplers application note.

ELECTRICAL CHARACTERISTICS ( $T_{amb} = 25\text{ °C}$ , unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
<b>INPUT</b>							
Forward voltage	$I_F = 10\text{ mA}$		$V_F$		1.2	1.4	V
Reverse current	$V_R = 6\text{ V}$		$I_R$		0.1	10	$\mu\text{A}$
Input capacitance	$V_F = 0\text{ V}$ , $f = 1\text{ MHz}$		$C_I$		25		pF
<b>OUTPUT</b>							
Repetitive peak off-state voltage	$I_{DRM} = 100\text{ }\mu\text{A}$	VO4154D/H/M	$V_{DRM}$	400			V
		VO4156D/H/M	$V_{DRM}$	600			V
Off-state current	$V_D = V_{DRM}$ , $I_F = 0\text{ A}$		$I_{DRM}$			100	$\mu\text{A}$
On-state voltage	$I_T = 300\text{ mA}$		$V_{TM}$			3	V
On-state current	$PF = 1$ , $V_{T(RMS)} = 1.7\text{ V}$		$I_{TM}$			300	mA
Off-state current in inhibit state	$I_F = 2\text{ mA}$ , $V_{DRM}$		$I_{DINH}$			200	$\mu\text{A}$
Holding current			$I_H$			500	$\mu\text{A}$
Zero cross inhibit voltage	$I_F = \text{rated } I_{FT}$		$V_{IH}$			20	V
Critical rate of rise of off-state voltage	$V_D = 0.67 V_{DRM}$ , $T_J = 25\text{ °C}$		$dV/dt_{cr}$	5000			V/ $\mu\text{s}$
Critical rate of rise of on-state			$dV/dt_{cr}$	8			A/ $\mu\text{s}$
<b>COUPLER</b>							
LED trigger current, current required to latch output	$V_D = 3\text{ V}$	VO4154D	$I_{FT}$			1.6	mA
		VO4154H	$I_{FT}$			2	mA
		VO4154M	$I_{FT}$			3	mA
		VO4156D	$I_{FT}$			1.6	mA
		VO4156H	$I_{FT}$			2	mA
		VO4156M	$I_{FT}$			3	mA
Common mode coupling capacitance			$C_{CM}$		0.01		pF
Capacitance (input to output)	$f = 1\text{ MHz}$ , $V_{IO} = 0\text{ V}$		$C_{IO}$		0.8		pF

**Note**

- Minimum and maximum values were tested requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

SAFETY AND INSULATION RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Climatic classification (according to IEC68 part 1)				55/100/21		
Pollution degree (DIN VDE 0109)				2		
Comparative tracking index per DIN IEC112/VDE 0303 part 1, group IIIa per DIN VDE 6110 175 399			175		399	
$V_{IOTM}$		$V_{IOTM}$	8000			V
$V_{IORM}$		$V_{IORM}$	890			V
$P_{SO}$		$P_{SO}$			500	mW
$I_{SI}$		$I_{SI}$			250	mA
$T_{SI}$		$T_{SI}$			175	°C
Creepage distance			7			mm
Clearance distance			7			mm

### TYPICAL CHARACTERISTICS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

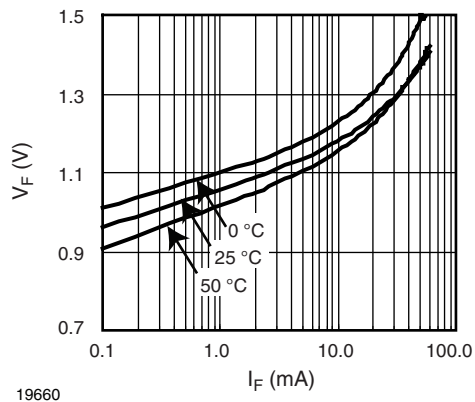


Fig. 2 - Diode Forward Voltage vs. Forward Current

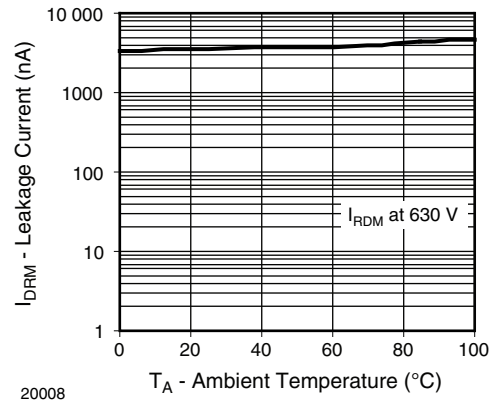


Fig. 4 - Leakage Current vs. Ambient Temperature

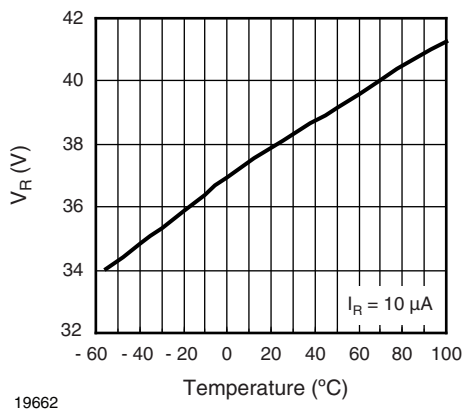


Fig. 3 - Diode Reverse Voltage vs. Temperature

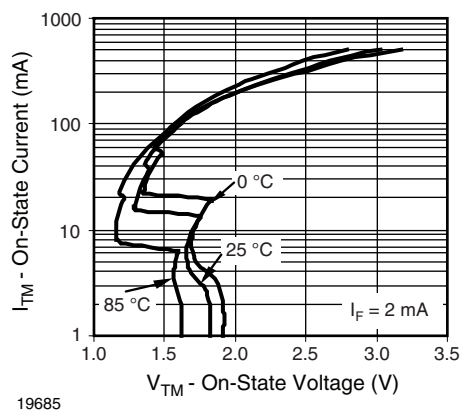
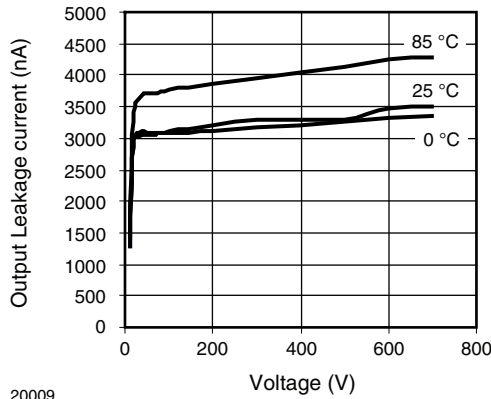


Fig. 5 - On-State Current vs. On-State Voltage

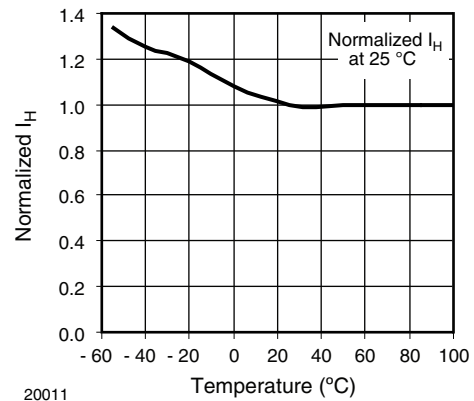


Optocoupler, Phototriac Output, Zero Crossing, High dV/dt, Low Input Current  
Vishay Semiconductors



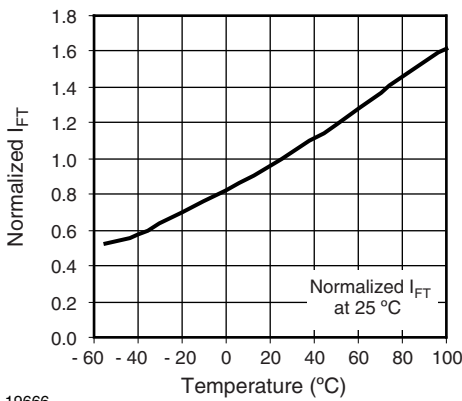
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Fig. 6 - Output Off Current (Leakage) vs. Voltage



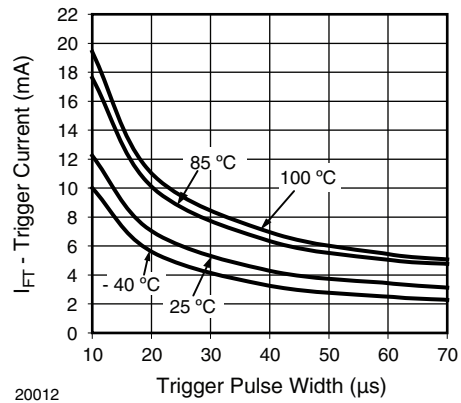
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Fig. 9 - Normalized Holding Current vs. Temperature



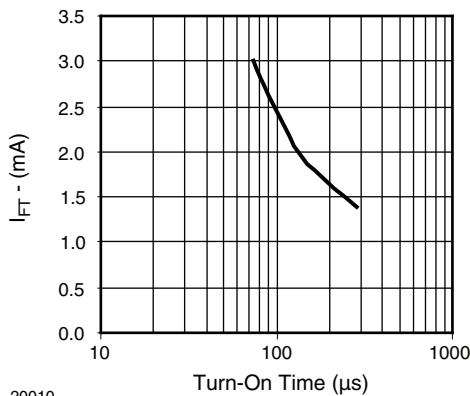
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Fig. 7 - Normalized Trigger Input Current vs. Temperature



20012

Fig. 10 - I<sub>FT</sub> vs. LED Pulse Width



20010

Fig. 8 - I<sub>FT</sub> (mA) vs. Turn-On Time (μs)



## Disclaimer

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